

## **MARIA KAYAMBAKI - PUBLICATIONS**

1. **M. Kayambaki**, N. Makris, K. Tsagaraki, H. Peyré, A. Stavrinidis, G. Konstantinidis, K. Zekentes  
*4H-SiC p-type doping determination from secondary electrons imaging*  
(2018) 12<sup>th</sup> European Conference on Silicon Carbide and Related Materials (ECSCRM)  
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2. Kazazis, S.A., Papadomanolaki, E., Androulidaki, M., **Kayambaki, M.**, Iliopoulos, E.  
*Optical properties of InGaN thin films in the entire composition range*  
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*A continuous semi-empirical VJFET capacitance model from sub to above threshold regime*  
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4. **Kayambaki, M.**, Makris, N., Stavrinidis, A., Konstantinidis, G., Zekentes, K.  
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5. Tsagaraki, K., Nafouti, M., Peyré, H., Vamvoukakis, K., Makris, N., **Kayambaki, M.**, Stavrinidis, A., Konstantinidis, G., Panagopoulou, M., Alquier, D., Zekentes, K.  
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*Investigation of thin InN/GaN heterostructures with in situ SiN<sub>x</sub> dielectric grown by plasma-assisted molecular beam epitaxy*  
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